

CoolMOS[®] Power Transistor
Features

- Lowest figure-of-merit $R_{ON} \times Q_g$
- Ultra low gate charge
- Extreme dv/dt rated
- High peak current capability
- Qualified according to JEDEC¹⁾ for target applications
- Pb-free lead plating; RoHS compliant

CoolMOS CP is designed for:

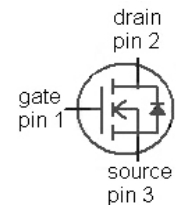
- Hard switching SMPS topologies

Product Summary

| | | |
|-------------------------------------|-----|----------|
| $V_{DS} @ T_{j,max}$ | 650 | V |
| $R_{DS(on),max} @ T_j = 25^\circ C$ | 0.6 | Ω |
| $Q_{g,typ}$ | 21 | nC |

PG-TO252


| Type | Package | Marking |
|-------------|----------|---------|
| IPD60R600CP | PG-TO252 | 6R600P |


Maximum ratings, at $T_j = 25^\circ C$, unless otherwise specified

| Parameter | Symbol | Conditions | Value | Unit |
|---|----------------|------------------------------|-------------|------------|
| Continuous drain current | I_D | $T_C = 25^\circ C$ | 6.1 | A |
| | | $T_C = 100^\circ C$ | 3.8 | |
| Pulsed drain current ²⁾ | $I_{D,pulse}$ | $T_C = 25^\circ C$ | 15 | |
| Avalanche energy, single pulse | E_{AS} | $I_D = 2.2 A, V_{DD} = 50 V$ | 144 | mJ |
| Avalanche energy, repetitive t_{AR} ^{2),3)} | E_{AR} | $I_D = 2.2 A, V_{DD} = 50 V$ | 0.2 | |
| Avalanche current, repetitive t_{AR} ^{2),3)} | I_{AR} | | 2.2 | A |
| MOSFET dv/dt ruggedness | dv/dt | $V_{DS} = 0 \dots 480 V$ | 50 | V/ns |
| Gate source voltage | V_{GS} | static | ± 20 | V |
| | | AC ($f > 1 Hz$) | ± 30 | |
| Power dissipation | P_{tot} | $T_C = 25^\circ C$ | 60 | W |
| Operating and storage temperature | T_j, T_{stg} | | -55 ... 150 | $^\circ C$ |

Maximum ratings, at $T_j=25\text{ °C}$, unless otherwise specified

| Parameter | Symbol | Conditions | Value | Unit |
|-------------------------------------|---------------|--------------------|-------|------|
| Continuous diode forward current | I_S | $T_C=25\text{ °C}$ | 3.3 | A |
| Diode pulse current ²⁾ | $I_{S,pulse}$ | | 15 | |
| Reverse diode dv/dt ⁴⁾ | dv/dt | | 15 | V/ns |

| Parameter | Symbol | Conditions | Values | | | Unit |
|-----------|--------|------------|--------|------|------|------|
| | | | min. | typ. | max. | |

Thermal characteristics

| | | | | | | |
|--|------------|--|---|----|-----|-----|
| Thermal resistance, junction - case | R_{thJC} | | - | - | 2.1 | K/W |
| Thermal resistance, junction - ambient | R_{thJA} | leaded | - | - | 62 | |
| | R_{thJA} | SMD version, device on PCB, minimal footprint | - | - | 62 | |
| | | SMD version, device on PCB, 6 cm ² cooling area ³⁾ | - | 35 | - | |

Electrical characteristics, at $T_j=25\text{ °C}$, unless otherwise specified
Static characteristics

| | | | | | | |
|----------------------------------|---------------|---|-----|------|-----|---------------|
| Drain-source breakdown voltage | $V_{(BR)DSS}$ | $V_{GS}=0\text{ V}, I_D=250\text{ }\mu\text{A}$ | 600 | - | - | V |
| Gate threshold voltage | $V_{GS(th)}$ | $V_{DS}=V_{GS}, I_D=220\text{ }\mu\text{A}$ | 2.5 | 3 | 3.5 | |
| Zero gate voltage drain current | I_{DSS} | $V_{DS}=600\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ °C}$ | - | - | 1 | μA |
| | | $V_{DS}=600\text{ V}, V_{GS}=0\text{ V}, T_j=150\text{ °C}$ | - | 10 | - | |
| Gate-source leakage current | I_{GSS} | $V_{GS}=20\text{ V}, V_{DS}=0\text{ V}$ | - | - | 100 | nA |
| Drain-source on-state resistance | $R_{DS(on)}$ | $V_{GS}=10\text{ V}, I_D=3.3\text{ A}, T_j=25\text{ °C}$ | - | 0.54 | 0.6 | Ω |
| | | $V_{GS}=10\text{ V}, I_D=3.3\text{ A}, T_j=150\text{ °C}$ | - | 1.5 | - | |
| Gate resistance | R_G | $f=1\text{ MHz}$, open drain | - | 1.5 | - | Ω |

| Parameter | Symbol | Conditions | Values | | | Unit |
|-----------|--------|------------|--------|------|------|------|
| | | | min. | typ. | max. | |

Dynamic characteristics

| | | | | | | |
|--|--------------|---|---|-----|---|----|
| Input capacitance | C_{iss} | $V_{GS}=0\text{ V}, V_{DS}=100\text{ V},$ $f=1\text{ MHz}$ | - | 550 | - | pF |
| Output capacitance | C_{oss} | | - | 28 | - | |
| Effective output capacitance, energy related ⁵⁾ | $C_{o(er)}$ | $V_{GS}=0\text{ V}, V_{DS}=0\text{ V}$ to 480 V | - | 26 | - | |
| Effective output capacitance, time related ⁶⁾ | $C_{o(tr)}$ | | - | 67 | - | |
| Turn-on delay time | $t_{d(on)}$ | $V_{DD}=400\text{ V},$ $V_{GS}=10\text{ V}, I_D=3.3\text{ A},$ $R_G=23.1\ \Omega$ | - | 17 | - | ns |
| Rise time | t_r | | - | 12 | - | |
| Turn-off delay time | $t_{d(off)}$ | | - | 75 | - | |
| Fall time | t_f | | - | 17 | - | |

Gate Charge Characteristics

| | | | | | | |
|-----------------------|---------------|--|---|-----|----|----|
| Gate to source charge | Q_{gs} | $V_{DD}=480\text{ V}, I_D=3.3\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$ | - | 2 | - | nC |
| Gate to drain charge | Q_{gd} | | - | 10 | - | |
| Gate charge total | Q_g | | - | 21 | 27 | |
| Gate plateau voltage | $V_{plateau}$ | | - | 4.7 | - | V |

Reverse Diode

| | | | | | | |
|-------------------------------|-----------|--|---|-----|-----|---------------|
| Diode forward voltage | V_{SD} | $V_{GS}=0\text{ V}, I_F=3.3\text{ A},$ $T_j=25\text{ }^\circ\text{C}$ | - | 0.8 | 1.2 | V |
| Reverse recovery time | t_{rr} | $V_R=400\text{ V}, I_F=I_S,$ $di_F/dt=100\text{ A}/\mu\text{s}$ | - | 220 | - | ns |
| Reverse recovery charge | Q_{rr} | | - | 2.3 | - | μC |
| Peak reverse recovery current | I_{rrm} | | - | 18 | - | A |

¹⁾ J-STD20 and JESD22

²⁾ Pulse width t_p limited by $T_{j,max}$

³⁾ Repetitive avalanche causes additional power losses that can be calculated as $P_{AV}=E_{AR} \cdot f$.

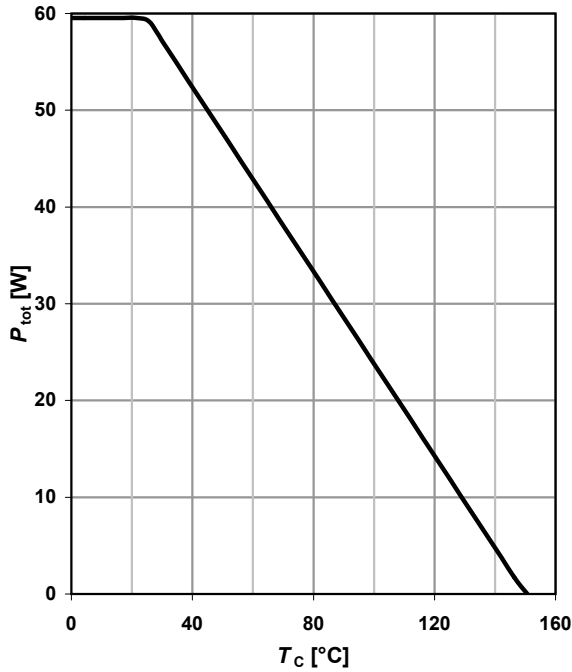
⁴⁾ $I_{SD}=I_D, di/dt \leq 400\text{ A}/\mu\text{s}, V_{DClink}=400\text{ V}, V_{peak} < V_{(BR)DSS}, T_j < T_{j,max}$, identical low side and high side switch

⁵⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

⁶⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

1 Power dissipation

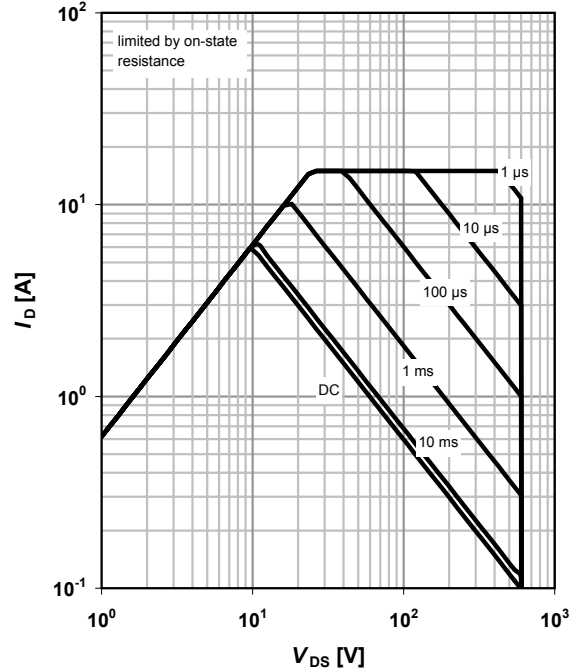
$P_{tot}=f(T_C)$



2 Safe operating area

$I_D=f(V_{DS}); T_C=25\text{ °C}; D=0$

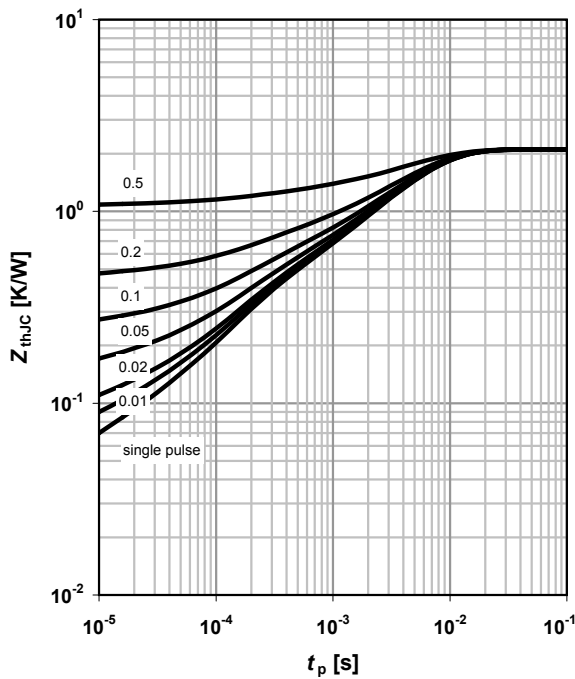
parameter: t_p



3 Max. transient thermal impedance

$Z_{thJC}=f(t_p)$

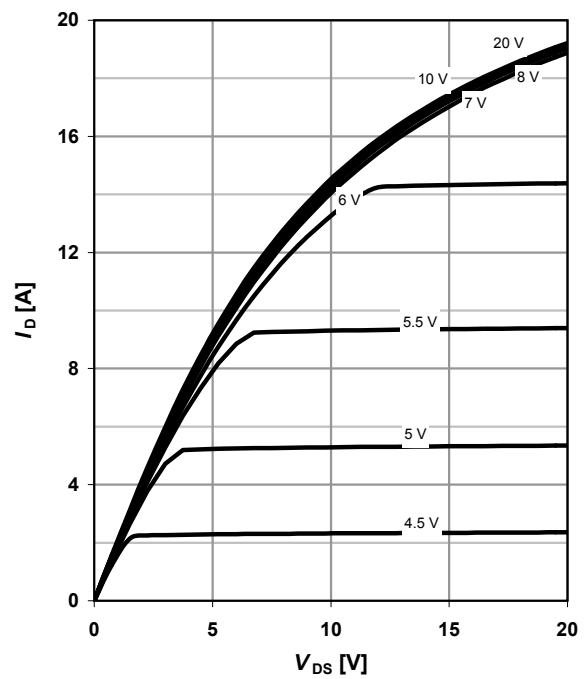
parameter: $D=t_p/T$



4 Typ. output characteristics

$I_D=f(V_{DS}); T_j=25\text{ °C}$

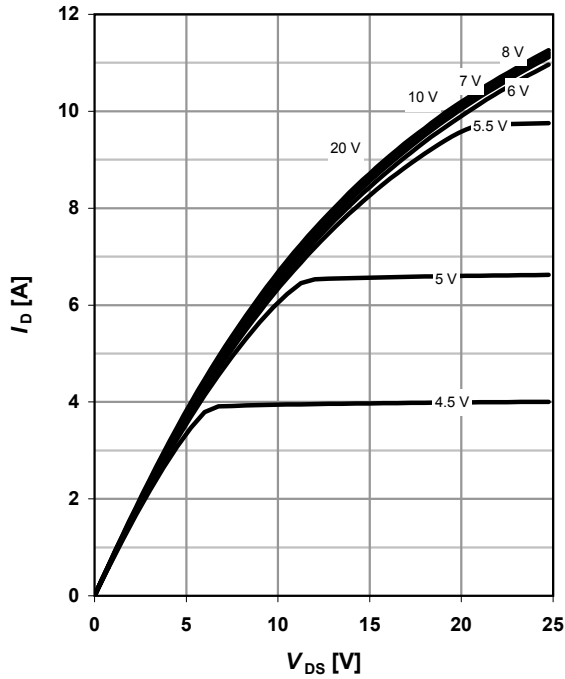
parameter: V_{GS}



5 Typ. output characteristics

$I_D = f(V_{DS}); T_j = 150\text{ }^\circ\text{C}$

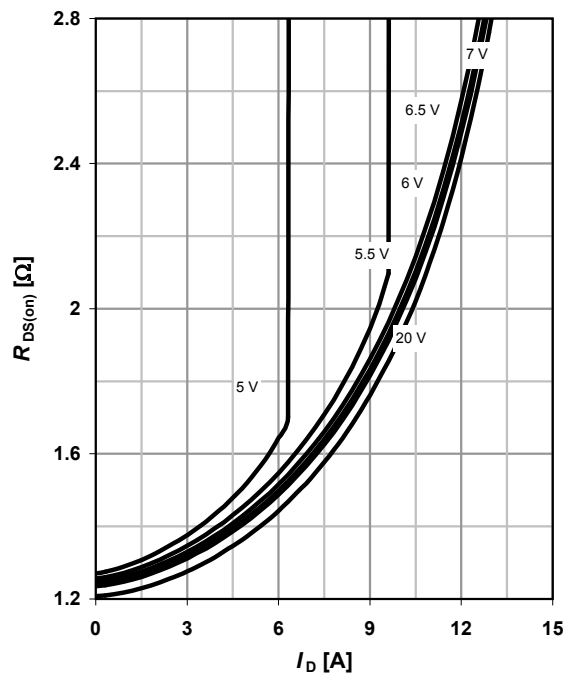
parameter: V_{GS}



6 Typ. drain-source on-state resistance

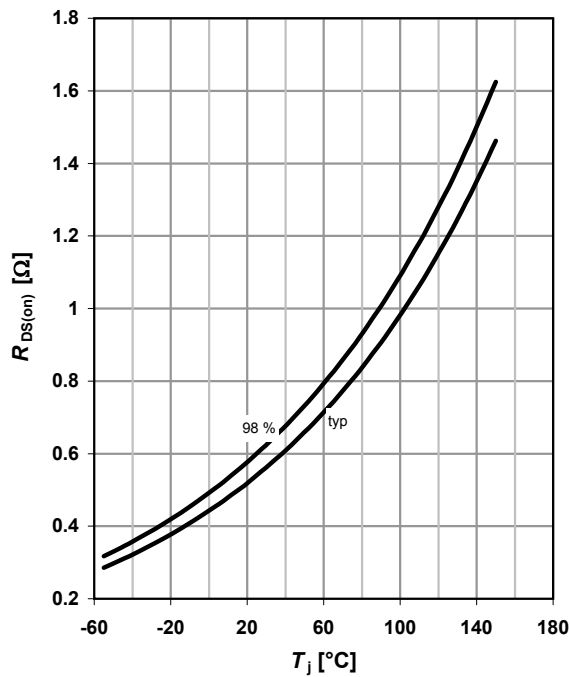
$R_{DS(on)} = f(I_D); T_j = 150\text{ }^\circ\text{C}$

parameter: V_{GS}



7 Drain-source on-state resistance

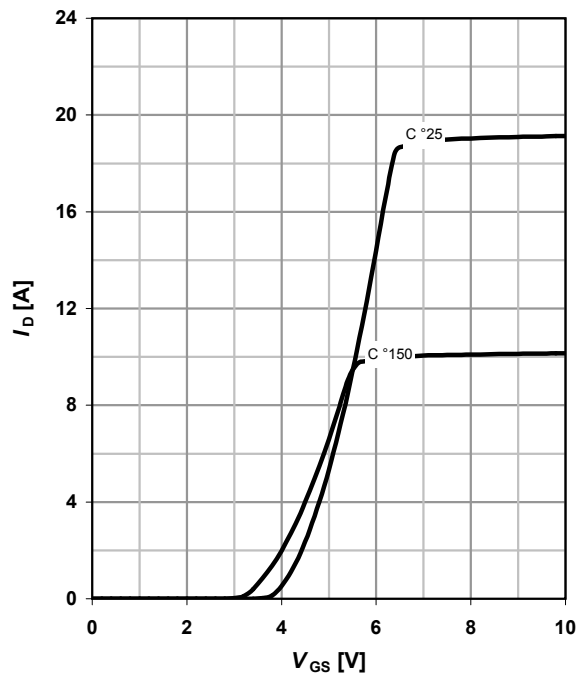
$R_{DS(on)} = f(T_j); I_D = 3.3\text{ A}; V_{GS} = 10\text{ V}$



8 Typ. transfer characteristics

$I_D = f(V_{GS}); |V_{DS}| > 2I_D/R_{DS(on)max}$

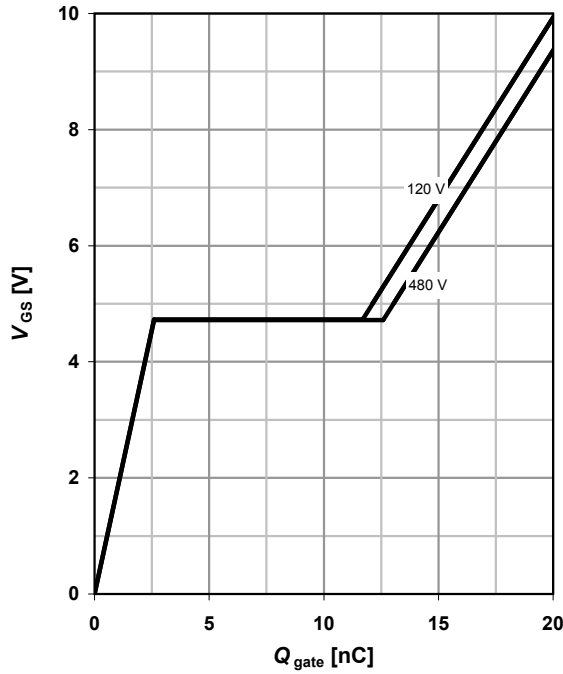
parameter: T_j



9 Typ. gate charge

$V_{GS}=f(Q_{gate}); I_D=3.3\text{ A pulsed}$

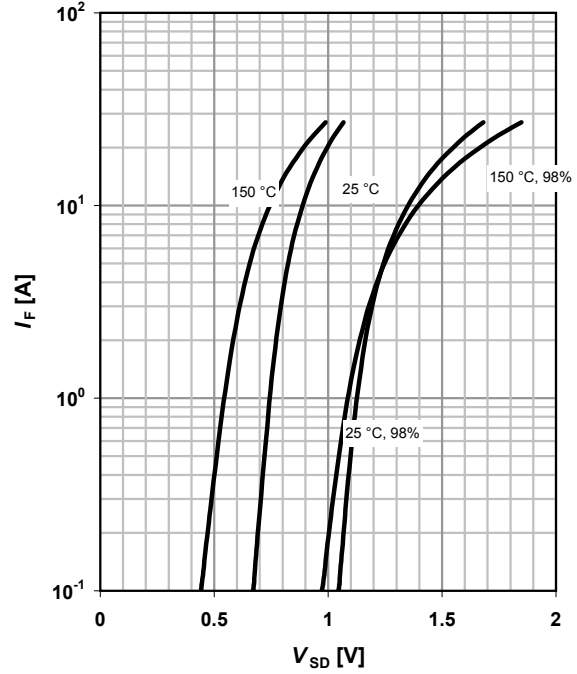
parameter: V_{DD}



10 Forward characteristics of reverse diode

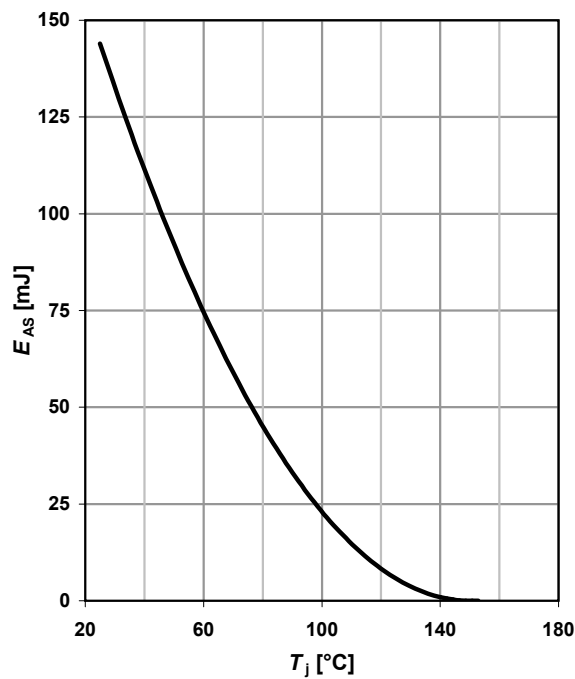
$I_F=f(V_{SD})$

parameter: T_j



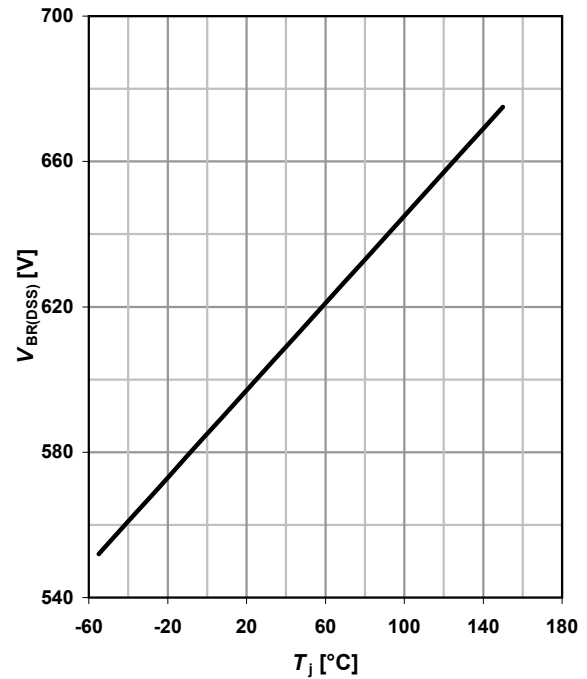
11 Avalanche energy

$E_{AS}=f(T_j); I_D=2.2\text{ A}; V_{DD}=50\text{ V}$



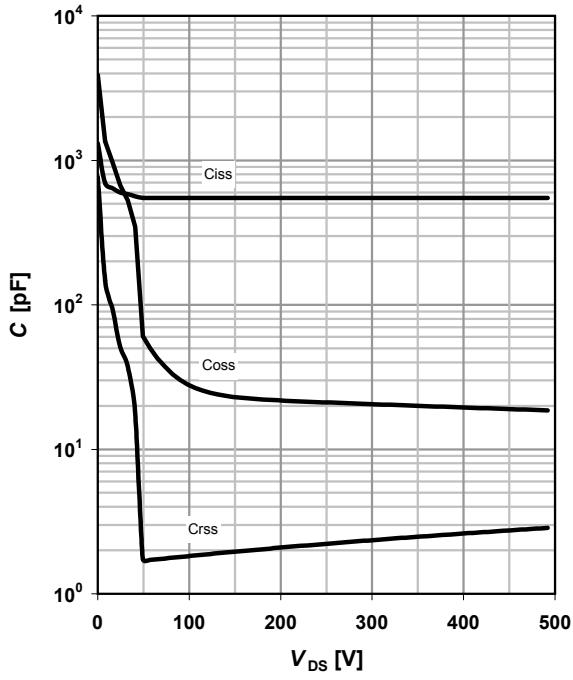
12 Drain-source breakdown voltage

$V_{BR(DSS)}=f(T_j); I_D=0.25\text{ mA}$



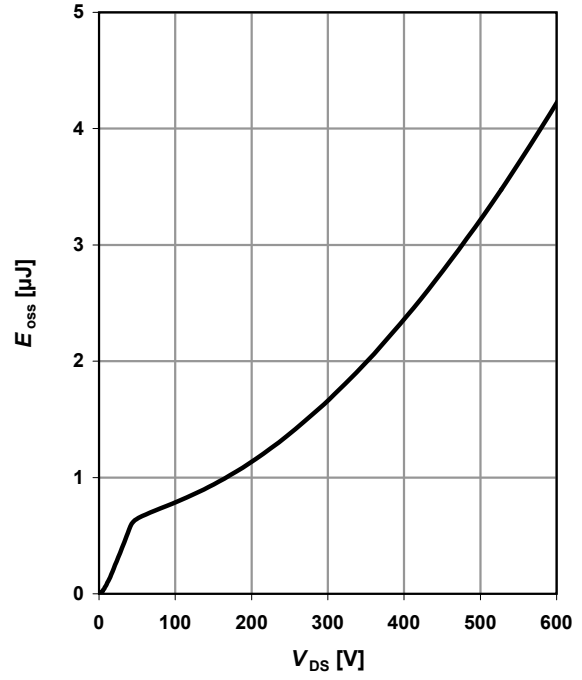
13 Typ. capacitances

$C=f(V_{DS}); V_{GS}=0\text{ V}; f=1\text{ MHz}$



14 Typ. Coss stored energy

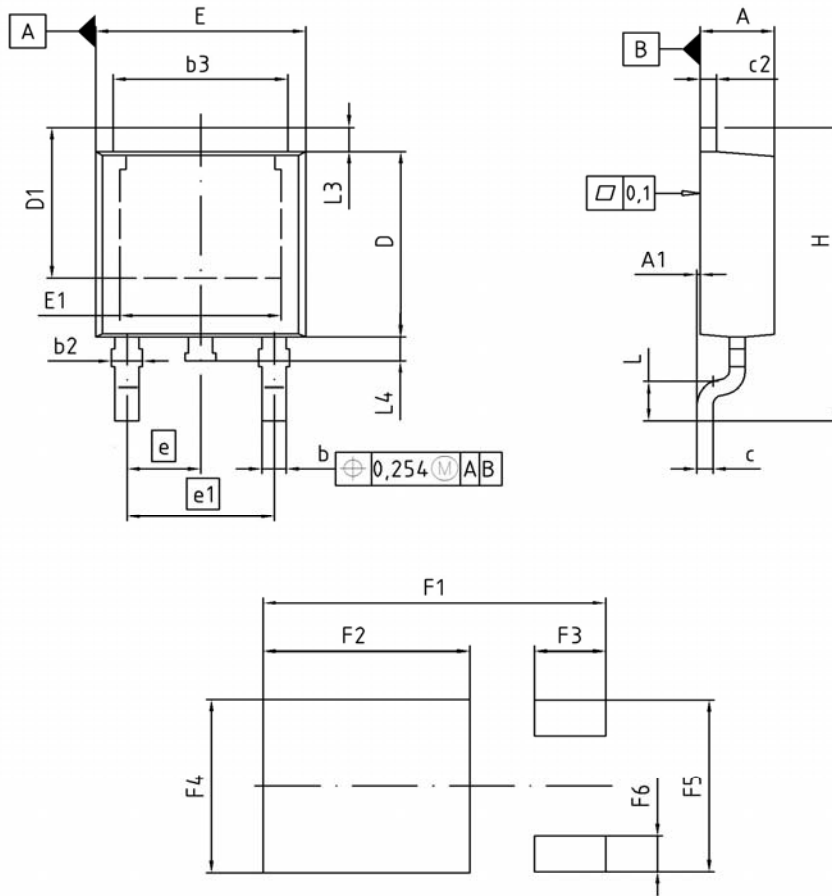
$E_{oss}=f(V_{DS})$



Definition of diode switching characteristics



PG-TO252: Outlines



| DIM | MILLIMETERS | | INCHES | |
|-----|-------------|-------|--------|-------|
| | MIN | MAX | MIN | MAX |
| A | 2.16 | 2.41 | 0.085 | 0.095 |
| A1 | 0.00 | 0.15 | 0.000 | 0.006 |
| b | 0.64 | 0.89 | 0.025 | 0.035 |
| b2 | 0.65 | 1.15 | 0.026 | 0.045 |
| b3 | 5.00 | 5.50 | 0.197 | 0.217 |
| c | 0.46 | 0.60 | 0.018 | 0.024 |
| c2 | 0.46 | 0.98 | 0.018 | 0.039 |
| D | 5.97 | 6.22 | 0.235 | 0.245 |
| D1 | 5.02 | 5.84 | 0.198 | 0.230 |
| E | 6.40 | 6.73 | 0.252 | 0.265 |
| E1 | 4.70 | 5.21 | 0.185 | 0.205 |
| e | 2.29 | | 0.090 | |
| e1 | 4.57 | | 0.180 | |
| N | 3 | | 3 | |
| H | 9.40 | 10.48 | 0.370 | 0.413 |
| L | 1.18 | 1.70 | 0.046 | 0.067 |
| L3 | 0.90 | 1.25 | 0.035 | 0.049 |
| L4 | 0.51 | 1.00 | 0.020 | 0.039 |
| F1 | 10.50 | 10.70 | 0.413 | 0.421 |
| F2 | 6.30 | 6.50 | 0.248 | 0.256 |
| F3 | 2.10 | 2.30 | 0.083 | 0.091 |
| F4 | 5.70 | 5.90 | 0.224 | 0.232 |
| F5 | 5.66 | 5.86 | 0.223 | 0.231 |
| F6 | 1.10 | 1.30 | 0.043 | 0.051 |

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